Metal coated DBR/DFB lasers

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Metallic nano-cavities can be used to fabricate lasers of sub-wavelength dimensions. Currently, these lasers emit their light through the substrate. This complicates measurements of these devices and their integration in optical systems. Side-emission offers a way to circumvent these problems. We plan to implement side-emission via distributed feedback; this allows accurate tuning of a cavity’s resonant wavelength and its emissive properties. In this paper we will give an update of the work that has been done.

Introduction

Sub-wavelength confinement of light in passive plasmonic devices, such as waveguides, has received considerable attention in the last couple of years [1, 2, 3]. For a long time it was believed that, due to the high optical loss, it was impossible to achieve lasing in a plasmonic cavity. However, Hill and colleagues have shown that it is possible to reproducibly fabricate plasmonic cavities with moderate Q-factors and that it is also possible to sustain a lasing mode inside such a cavity [4, 5].

The devices made by Hill are circular and rectangular shaped, with dimensions down to 80 nm, and are fully enclosed in silver. The devices are characterized by collecting light scattered through the substrate on which they are fabricated. To open the way for integration of these lasers in optical systems, side-emission is required. We believe that distributed feedback is suitable to enable side-emission in plasmonic cavities and propose to implement this via incorporation of vertical groove gratings in the cavity.

Basic device architecture

The general device architecture is shown in figure 1. The metallic nano-lasers are fabricated on a semi-insulating susbrate with an InP/InGaAs/InP double hetero junction.

An ultra-thin Si$_3$N$_4$ ($\leq 20$ nm) electrically isolates the semiconductor structure from the metal cladding. This Si$_3$N$_4$ layer also passivates surface damage caused by the etching of the devices.

After the insulation is applied, the whole structure is encapsulated in silver. The silver cladding also serves as the electrical n-contact of the device; the p-contact is located next to the device to allow scattering of light through the substrate. So far, the devices were always circular or rectangular shaped.

![figure 1: Schematic device overview](image-url)
Side-emitting metallic waveguide lasers

The first side-emitting lasers are simple Fabry-Perot type cavities. After cleaving, the end facet was polished in a cross-section polisher (figure 2); the width of the waveguide core is 240 nm. Figure 3 shows the lasing spectrum at a current of 0.8 mA. Lasing operation was achieved at a temperature of 80K.

Plasmon nano-lasers

To ensure that the propagating mode in the laser cavity is indeed the fundamental plasmon mode of the structure, the width of the waveguide has to be such that it is below cut-off of the 1st order plasmon mode and below the cut-off of the fundamental TE mode of the waveguide. For operation at 1550 nm, the waveguide widths that satisfy these conditions were determined from 2-D FDTD simulations [6] and were found to be ±140 nm, for a waveguide with a 20 nm thick Si$_3$N$_4$ insulation layer and ±150 nm for a waveguide with a 10 nm thick insulation.

Distributed Feedback

Distributed Bragg reflectors (DBR) and distributed feedback (DFB) are widely employed in semiconductor lasers to achieve single-mode operation or to control the amount of feedback into the laser cavity.

We have determined the optimum period of a Bragg grating to be approximately 220 nm for operation at 1550 nm. Incorporating such a grating in a metallic-coated cavity, a Q of over 200 can easily be achieved.
Incorporation of Bragg reflectors in a nano-cavity, however, is difficult since the grating and cavity cannot be separated from each other in terms of gain. Also the cavity and grating have to be terminated very accurately, in order not to disturb the phase condition required for Bragg reflectors.

Distributed feedback lasers are less sensitive to reflections caused by termination of the laser, provided that \( \kappa_L > 1 \) for the grating [7]. Normal DFB lasers support two modes (1st order operation), one on either side of the stop-band. Single mode operation, at the Bragg wavelength, can be forced by either applying a \( \lambda/4 \)-shift inside the laser cavity (figure 7) or making the laser asymmetric (e.g. by covering one facet with silver and removing it from the other facet).

We have determined the optimum period for operation at 1550 nm to be ±220 nm for a core waveguide width of 80 nm and the total width of the grating is chosen to be 130 nm (=80 nm core + 50 nm grating).

**Fabrication**

Definition of the devices by means of EBL in combination with lift-off is impossible for devices with these dimensions. The feature size is in the same order of magnitude as the thickness of the metal layer normally used to perform lift-off with.

Hydroxy Silsesquioxane (HSQ) is an electron beam resist with excellent lateral contrast, but with a rather low sensitivity [8, 9]. We use this resist to define devices with the desired dimensions. A top view of such a resist pattern, after litho and development is shown in figure 6a. The thickness of the HSQ layer is 80-120 nm. As can be seen from figure 6a, the small dimensions can be obtained without problems. The dose used to obtain these dimensions is around 3000 \( \mu \)C/cm\(^2\).

The HSQ is used to etch an underlying metal layer, which in its turn is used to transfer the pattern to a SiO\(_2\) hardmask layer, by means of a pure CHF\(_3\) process in a dedicated reactive ion etcher (RIE). This hardmask can then be used to etch the semiconductor material in a CH\(_4\)/H\(_2\) ICP-RIE.
Conclusions and outlook

Side-emission of metallic-coated laser cavities is possible. Distributed feedback is suitable to achieve single mode operation of these cavities. We have determined the approximate maximum width of the structure to guarantee plasmonic behaviour. We have also determined the grating dimensions required for operation at the desired wavelength of 1550 nm, taking into account the restrictions for plasmonic behavior. Simulations need to be refined incorporating gain, dispersion and fabrication imperfections. Finally, we have also shown that is possible to achieve the resolution required for the fabrication of these devices in our lithography process.

References


